

PHC2300

Complementary enhancement mode MOS transistors

Rev. 05 — 24 February 2011

Product data sheet

1. Product profile

1.1 General description

One N-channel and one P-channel enhancement mode Field-Effect Transistor (FET) in a plastic package. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

 Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- High-speed line drivers
- Line transformer drivers

- Relay drivers
- Universal line interface in telephone sets

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS} drain-source voltage		$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C};$ N-channel		-	-	300	V
		$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C};$ P-channel		-	-	-300	V
I _D	drain current	T _{sp} = 80 °C; N-channel	[1]	-	-	340	mΑ
		T _{sp} = 80 °C; P-channel	[1]	-	-	-235	mΑ
P _{tot}	total power dissipation	T _{sp} = 80 °C	[2]	-	-	1.6	W
Static char	acteristics						
R _{DSon}	R _{DSon} drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 170 \text{ mA};$ $T_j = 25 ^{\circ}\text{C}; \text{ N-channel}$		-	-	6	Ω
resistance		$V_{GS} = -10 \text{ V}; I_D = -115 \text{ mA};$ $T_j = 25 ^{\circ}\text{C}; P-channel}$		-	-	17	Ω



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic c	haracteristics					
Q _{GD} gate-drain charge	$V_{GS} = -10 \text{ V; } I_D = -115 \text{ mA;}$ $V_{DS} = -50 \text{ V; } T_j = 25 \text{ °C;}$ P-channel	-	674	-	pC	
		$V_{GS} = 10 \text{ V; } I_{D} = 170 \text{ mA;}$ $V_{DS} = 50 \text{ V; } T_{j} = 25 \text{ °C;}$ N-channel	-	1385	-	pC

- [1] Solder point temperature is the temperature at the soldering point of the drain leads.
- [2] Maximum permissible dissipation per MOS transistor (both devices may thus be loaded up to 1.6 W at the same time).

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D4 D4 D0 D0
2	G1	gate1	8 <u> </u>	D1 D1 D2 D2
3	S2	source2		
4	G2	gate2		
5	D2	drain2	1	S1 G1 S2 G2
6	D2	drain2	SOT96-1 (SO8)	sym114
7	D1	drain1		
8	D1	drain1		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHC2300	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

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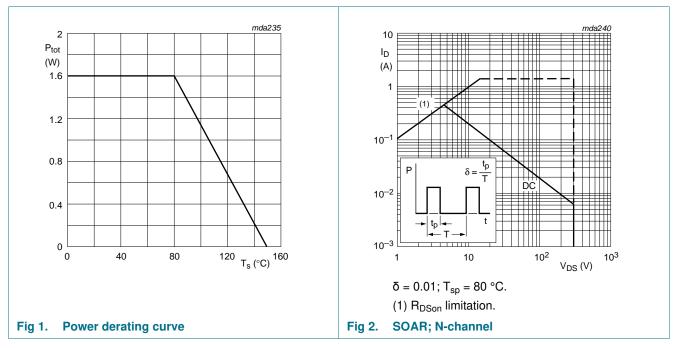
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C; N-channel	-	300	V
		$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; P-channel}$	-	-300	٧
V_{GS}	gate-source voltage		-20	20	٧
I _D drain current	drain current	T _{sp} = 80 °C; N-channel	<u>[1]</u> -	340	mA
	T _{sp} = 80 °C; P-channel	<u>[1]</u> -	-235	mA	
I _{DM} peak drain current	T _{sp} = 25 °C; pulsed; N-channel	[2] _	1.4	Α	
		T _{sp} = 25 °C; pulsed; P-channel	[2] _	-0.9	Α
P _{tot}	total power dissipation	$T_{sp} = 80 ^{\circ}C$	<u>[3]</u> _	1.6	W
		T _{amb} = 25 °C	<u>[4]</u> _	1.8	W
		T _{amb} = 25 °C	<u>[5]</u> _	0.9	W
		T _{amb} = 25 °C	<u>[6]</u> _	1.2	W
T _{stg}	storage temperature		-55	150	°C
Tj	junction temperature		-55	150	°C
_1 _j	Junction temperature		-55	150	

- [1] Solder point temperature is the temperature at the soldering point of the drain leads.
- [2] Pulse width and duty cycle limited by maximum junction temperature.
- [3] Maximum permissible dissipation per MOS transistor (both devices may thus be loaded up to 1.6 W at the same time).
- [4] Maximum permissible dissipation per MOS transistor. Value based on a printed-circuit board with an R_{th(a-tp)} (ambient to tie-point) of 27.5 K/W.
- [5] Maximum permissible dissipation per MOS transistor. Value based on a printed-circuit board with an R_{th(a-tp)} (ambient to tie-point) of 90 K/W.
- [6] Maximum permissible dissipation if only one MOS transistor dissipates. Value based on a printed-circuit board with an R_{th(a-tp)} (ambient to tie-point) of 90 K/W.

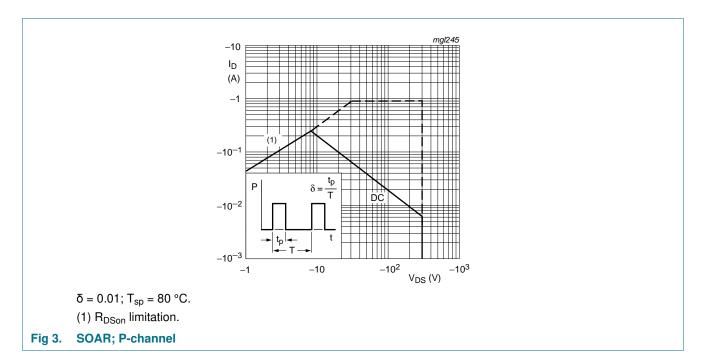


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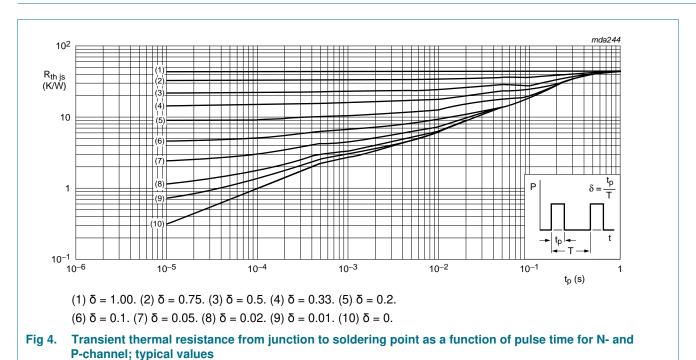
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from		-	-	43	K/W
	junction to solder point					



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6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -10 μ A; V_{GS} = 0 V; T_j = 25 °C; P-channel	-300	-	-	V
		I_D = 10 $\mu A;~V_{GS}$ = 0 V; T_j = 25 °C; N-channel	300	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; N-channel	0.8	-	2	V
		I_D = -1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; P-channel	-0.8	-	-2	V
I _{DSS}	drain leakage current	V_{DS} = -240 V; V_{GS} = 0 V; T_j = 25 °C; P-channel	-	-	-100	nA
		V_{DS} = 240 V; V_{GS} = 0 V; T_j = 25 °C; N-channel	-	-	100	nA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C; N-channel	-	-	100	nA
	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C; N-channel	-	-	100	nA	
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C; P-channel	-	-	100	nA
	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C; P-channel	-	-	100	nA	
R _{DSon} drain-source on-state resistance	V_{GS} = 10 V; I_D = 170 mA; T_j = 25 °C; N-channel	-	-	6	Ω	
		V_{GS} = -10 V; I_D = -115 mA; T_j = 25 °C; P-channel	-	-	17	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I_D = 170 mA; V_{DS} = 50 V; V_{GS} = 10 V; T_j = 25 °C; N-channel	-	6240	-	pC
		I_D = -115 mA; V_{DS} = -50 V; V_{GS} = -10 V; T_j = 25 °C; P-channel	-	2137	-	pC
Q_{GS}	gate-source charge	$I_D = 170 \text{ mA}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 ^{\circ}\text{C}; \text{ N-channel}$	-	226	-	рС
		$I_D = -115 \text{ mA}$; $V_{DS} = -50 \text{ V}$; $V_{GS} = -10 \text{ V}$;	-	68	-	рС
Q_{GD}	gate-drain charge	T _j = 25 °C; P-channel	-	674	-	рС
		I_D = 170 mA; V_{DS} = 50 V; V_{GS} = 10 V; T_j = 25 °C; N-channel	-	1385	-	рС
C _{iss}	input capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; N-channel	-	102	-	pF
		V_{DS} = -50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; P-channel	-	45	-	pF
C _{oss}	output capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ N-channel}$	-	15	-	pF
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; P\text{-channel}$	-	15	-	pF
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 Table 6.
 Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C_{rss}	reverse transfer capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; N-channel	-	7.3	-	pF
		V_{DS} = -50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; P-channel	-	3	-	pF
t _{on} turn-on time	turn-on time	V_{DS} = 50 V; V_{GS} = 10 V; I_D = 170 mA; T_j = 25 °C; N-channel	-	7	12	ns
		V_{DS} = -50 V; V_{GS} = -10 V; I_{D} = -115 mA; T_{j} = 25 °C; P-channel	-	4	10	ns
t _{off} turn-off time		V_{DS} = 50 V; V_{GS} = 10 V; T_j = 25 °C; I_D = 170 mA; N-channel	-	53	65	ns
		V_{DS} = -50 V; V_{GS} = -10 V; T_j = 25 °C; I_D = -115 mA; P-channel	-	25	35	ns

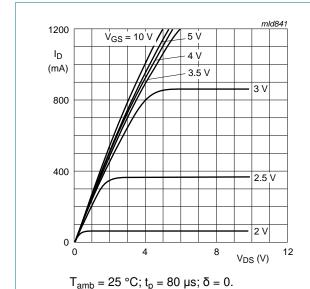
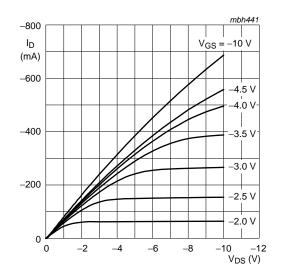


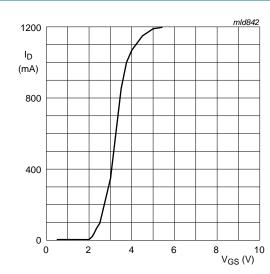
Fig 5. Output characteristics: drain current as a function of drain-source voltage; N-channel; typical values



 T_{amb} = 25 °C; t_p = 80 μ s; δ = 0.

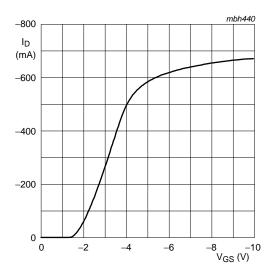
Fig 6. Output characteristics: drain current as a function of drain-source voltage; P-channel; typical values

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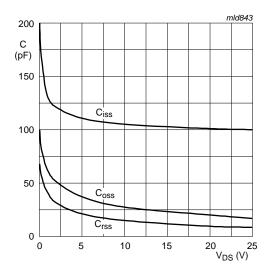
 V_{DS} = 10 V; T_{amb} = 25 °C; t_p = 80 $\mu s;$ δ = 0.

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; N-channel; typical values



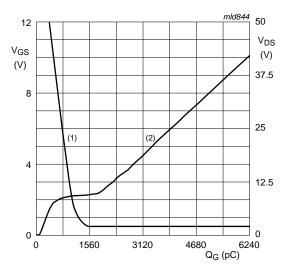
 V_{DS} = -10 V; T_{amb} = 25 °C; t_p = 80 μs ; δ = 0.

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; P-channel; typical values



 $T_{amb} = 25^{\circ}C; f = 1MHz$

Fig 9. Input, output and reverse transfer capacitances as a function of drain-source voltage;
N-channel; typical values



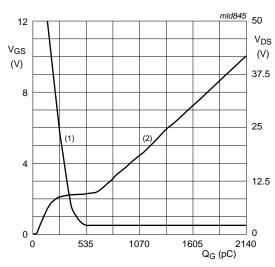
 $V_{DS} = 50 \text{ V}; I_D = 170 \text{ mA}; T_{amb} = 25 \text{ °C}.$

 $(1) V_{DS}$

(2) V_{GS}

Fig 10. Gate-source voltage and drain-source voltage as a function of gate charge; N-channel typical values

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 V_{DS} = -50 V; I_D = -115 mA; T_{amb} = 25 °C.

- $(1) V_{DS}$
- (2) V_{GS}

Fig 11. Gate-source voltage and drain-source voltage as a function of gate charge; P-channel typical values

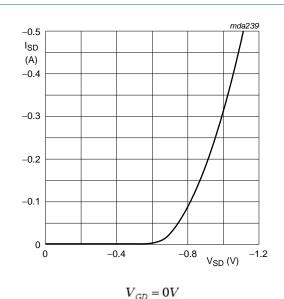
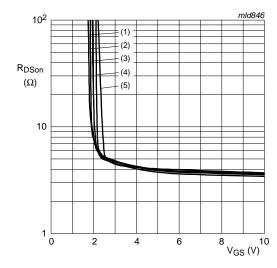


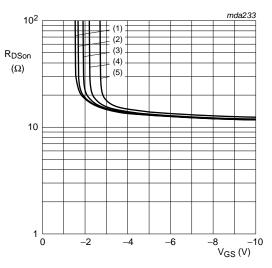
Fig 12. Source current as a function of source-drain voltage; P-channel typical values



 $V_{DS} \ge I_D X R_{DSon}$; $T_{amb} = 25 \, ^{\circ}C$; $t_p = 300 \, \mu s$; $\delta = 0$.

- (1) $I_D = 10 \text{ mA}$.
- (2) $I_D = 20 \text{ mA}$.
- (3) $I_D = 50 \text{ mA}$.
- (4) $I_D = 100 \text{ mA}$.
- (5) $I_D = 200 \text{ mA}$.

Fig 13. Drain-source on-state resistance as a function of gate-source voltage; N-channel typical values



 $V_{DS} \ge I_D X R_{DSon}$; $T_{amb} = 25 \, ^{\circ}C$; $t_p = 300 \, \mu s$; $\delta = 0$.

- (1) $I_D = -10 \text{ mA}$.
- (2) $I_D = -20 \text{ mA}$.
- (3) $I_D = -50 \text{ mA}$.
- (4) $I_D = -100 \text{ mA}$.
- (5) $I_D = -200 \text{ mA}$.

Fig 14. Drain-source on-state resistance as a function of gate-source voltage; P-channel typical values

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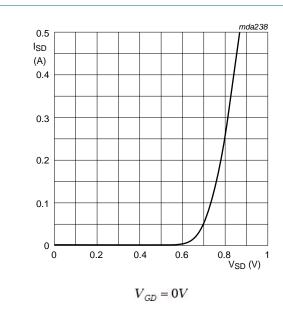


Fig 15. Source-drain current as a function of source-drain diode voltage; N-channel; typical values

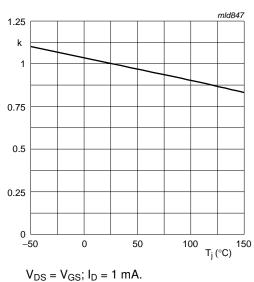


Fig 16. Temperature coefficient of gate-source threshold voltage as a function temperature; N-channel; typical values

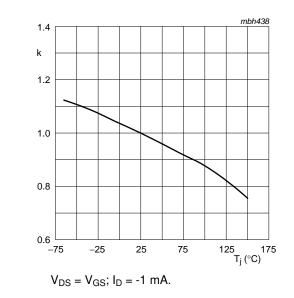
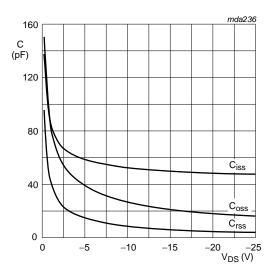


Fig 17. Temperature coefficient of gate-source threshold voltage as a function temperature; P-channel; typical values



 $T_{amb} = 25^{\circ}C; f = 1MHz$

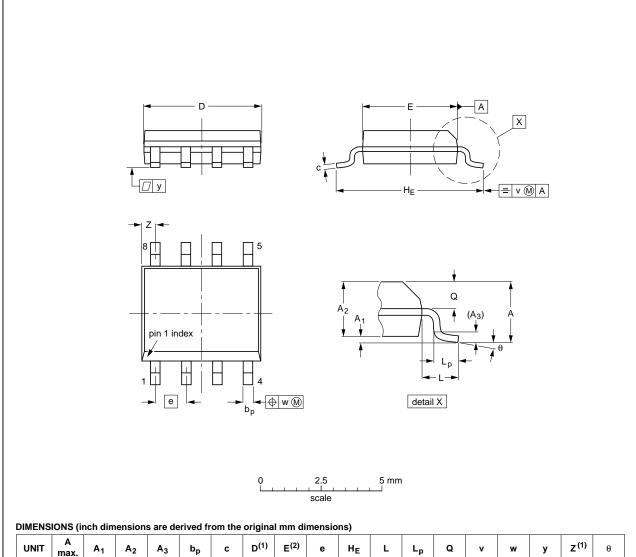
Fig 18. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT96-1	076E03	MS-012			99-12-27 03-02-18	

Fig 19. Package outline SOT96-1 (SO8)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHC2300 v.5	20110224	Product data sheet	-	PHC2300 v.4
Modifications:	 Various chang 	es to content.		
PHC2300 v.4	20101216	Product data sheet	-	PHC2300 v.3

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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